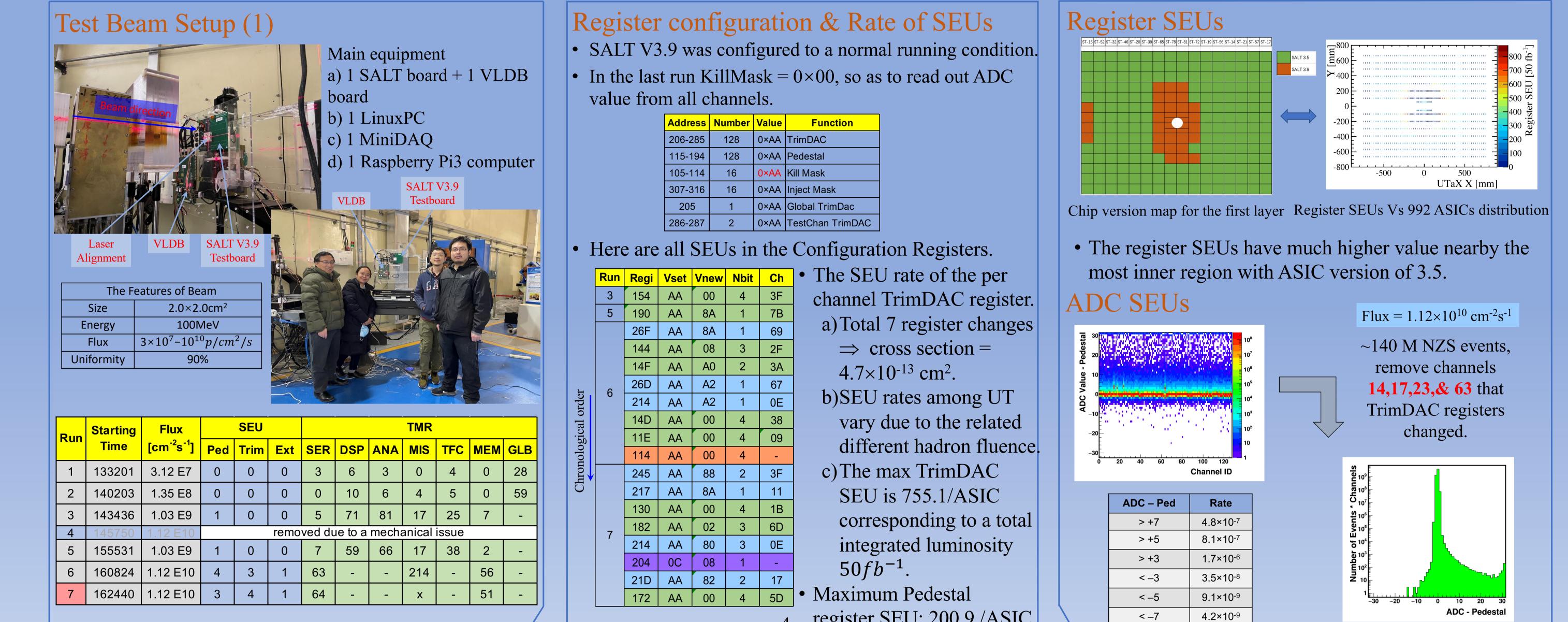
Radiation Study of the LHCb UT front-end readout ASIC

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Run Starting Flux		SEU		TMR								
ixun	Time	[cm ⁻² s ⁻¹]	Ped	Trim	Ext	SER	DSP	ANA	MIS	TFC	MEM	GLB
1	133201	3.12 E7	0	0	0	3	6	3	0	4	0	28
2	140203	1.35 E8	0	0	0	0	10	6	4	5	0	59
3	143436	1.03 E9	1	0	0	5	71	81	17	25	7	-
4	145750	1.12 E10	removed due to a mechanical issue									
5	155531	1.03 E9	1	0	0	7	59	66	17	38	2	-
6	160824	1.12 E10	4	3	1	63	-	-	214	-	56	-
7	162440	1.12 E10	3	4	1	64	-	-	х	-	51	-

- Calibration with a Faraday cup was performed for each intensity value.
- The total fluence for SEU test is 1.48×10^{13} cm⁻², 45.5% with KillMask.

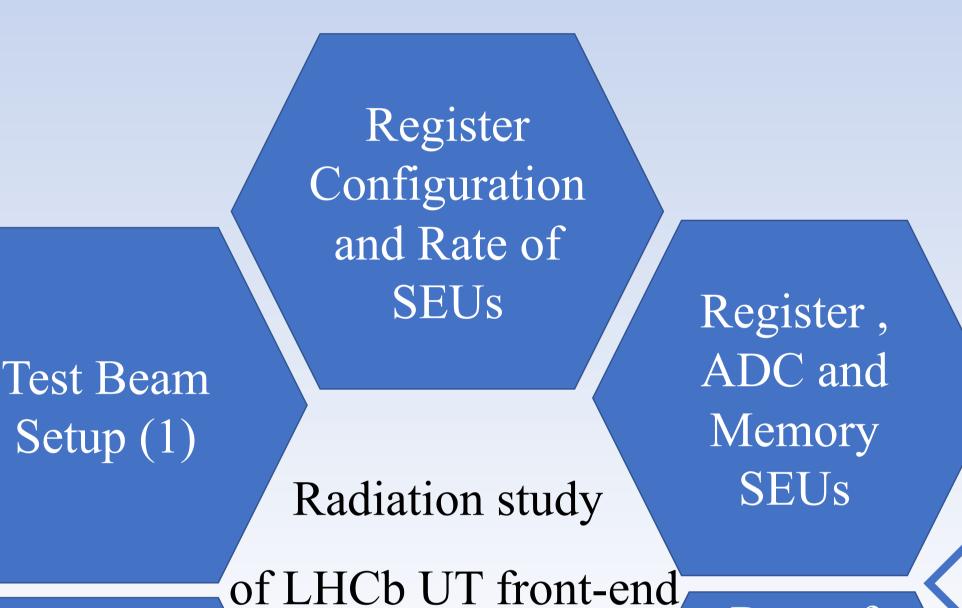


- **UT**(Upstream Tracker) is a new silicon strip tracker in LHCb upgrade I.
- It has 4 layers, each layer consists of 16/18 staves, and each stave consists of 14/16 hybrids.
- **SALT** (Silicon ASIC for LHCb Tracker) is the front end readout ASIC of the UT

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register SEU: 200.9 /ASIC.

Register SEU Test @CIAE



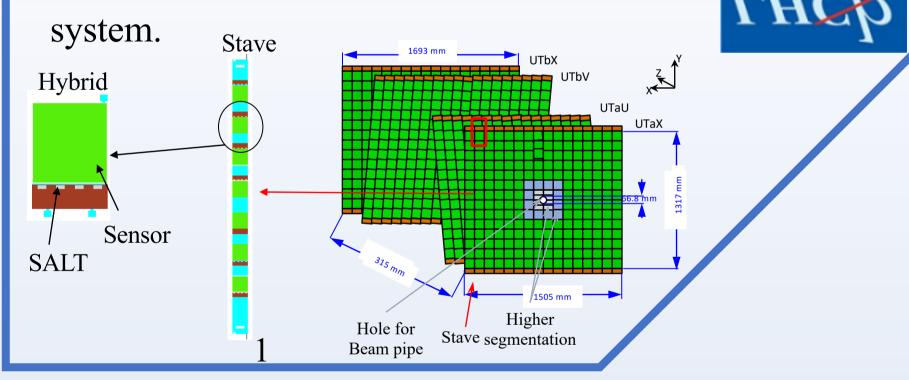
Memory SEUs

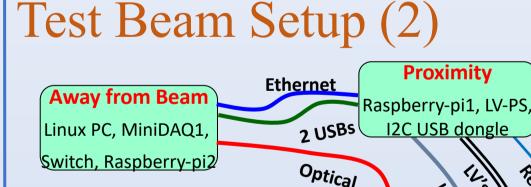
- Contraction

• 2 memory SEUs were observed, so we did another beam test at Dongguan to check more about memory SEUs.

Motivation

- SALT V3.5 is vulnerable to radiation in its TrimDAC and Pedestal registers. The cross sections are 7.8×10^{-11} cm² and 1.3×10^{-11} cm², respectively.
- SALT V3.9 was also tested twice.





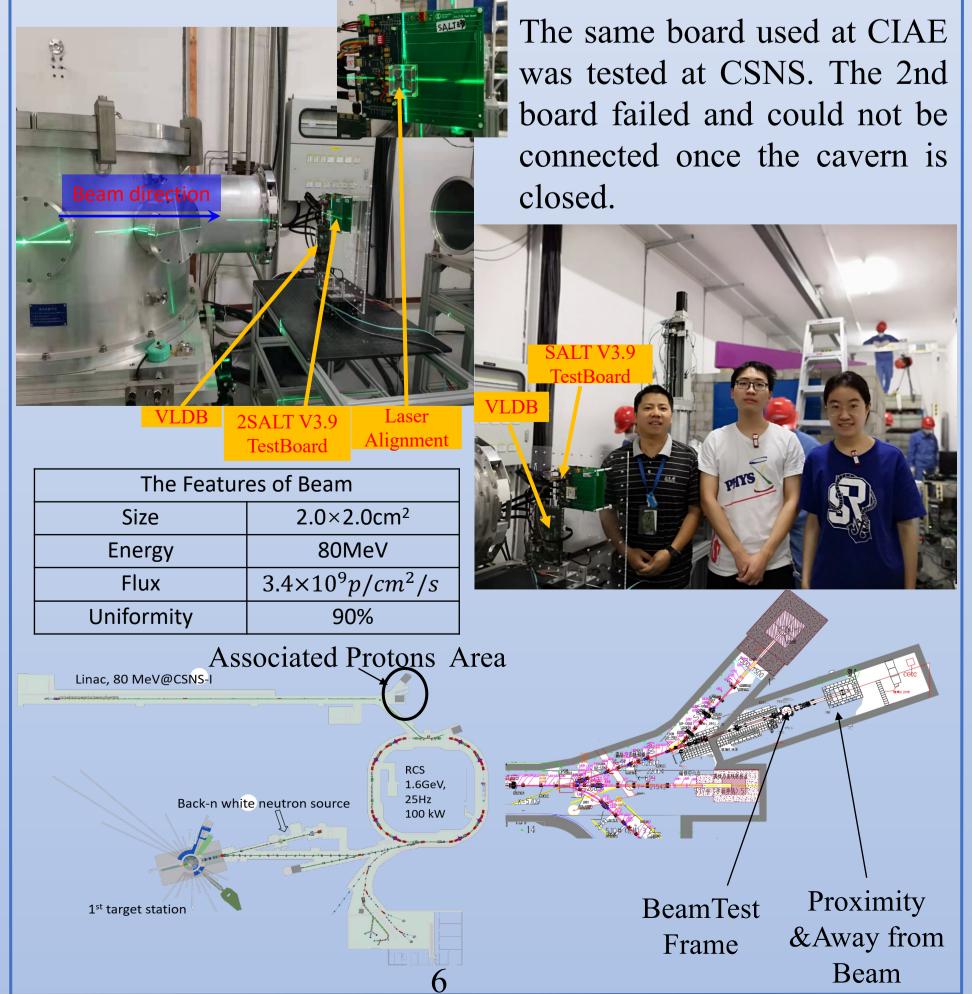
Control Room Switch for PS, Win-PCs

The two layouts are basically similar, except that we added an extra Beam Frame raspberry-pi to reset the VLDB, SALT-TB CCPC of the MiniDAQ.

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Test Beam

Setup (2)



Rate of readout ASIC Memory SEUs, Summary Two and Configuration Conclusion Modes and Calculation Model

Memory SEU Test @CSNS

Two Configuration Modes & Calculation Model

- SALT V3.9 was set to a special mode that the ADC value is constant 0x15.
- In order to calculate the rate of SEUs occurring during memory or data transfer, we planned two different configurations, difference between which is the time of data in the memory~6 times. DAQ Configuration: \Box MEP size of N × 480 BXs. \Box TFC sequence= 6*(1 NZS + 79 HeaderOnly).
 - Average time in memory: 81.4*25ns

The first was at the **CIAE** (China Institute of Atomic Energy) on Dec 31, 2020.

The second was at the **CSNS** (China Spallation Neutron Source) from Oct 18 to 25, 2021.

Rate of Memory SEUs

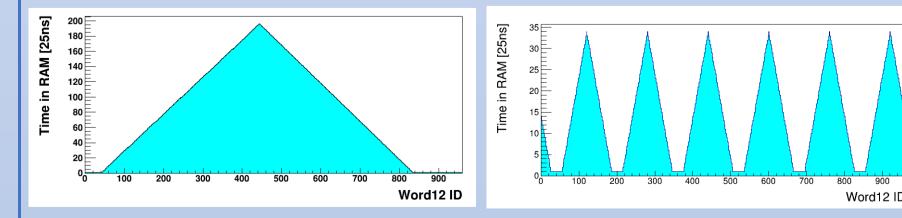
The cross section of data during transfer is much larger (~ 100 times) than that in memory. Take the cross section of data transfer as the total cross section.

- The SEU rate of the per channel in data transfer: a) cross section $\sigma_{total} = 5.9 \times 10^{-14} cm^2$.
- b) The maximum memory SEU is 19.4/ASIC corresponding to a total integrated luminosity $50fb^{-1}$.

Summary of SEUs (a) $50fb^{-1}$

	aX	aU	bV	bX
Total ASIC	992	992	1104	1104
SALT V3.9	224	248	200	224
SALT V3.5	768	744	904	880
Average TrimDAC SEU (/ASIC)	126.5	122.2	125.2	124.0
Average Pedestal SEU (/ASIC)	25.5	24.8	24.8	24.6
Average Memory SEU (/ASIC)	2.2	2.0	2.4	2.1

TFC sequence= (1 NZS + 79 HeaderOnly). Average time in memory: 14.4*25ns



Memory-dominated Mode Transfer-dominated Mode • During the process of fetching data, the beam flux was maintained at $3.4 \times 10^9 p/cm^2/s$. There are 10 and 7 SEUs observed in the two modes respectively.

• Calculation Model

 $N_1 = N_1^{RAM} + N_1^{Trans}$ $N_2 = N_2^{RAM} + N_2^{Trans}$ $N^{RAM} \propto T \times \sigma_{RAM} \times fluence$ $N^{Trans} \propto \sigma_{Trans} \times fluence$

Conclusion

- The rate of SEUs is low enough to LHCb.
- SALT has excellent performance in radiation resistance. Acknowledgements
- Thanks to everyone for helping set up a system at Beijing, especially Zhuoming Li, Federico Alessio, Paolo Durante, Ken Wyllie, Carlos Abellan, Will Parker, CIAE and CSNS colleagues.

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